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ABSTRACT

A structure is formed in an integrated circuit to provide for the coupling of elements in the integrated circuit. The structure extends from a conductive surface through a channel extending above the conductive surface. The structure includes a layer of a refractory metal, a layer of a metal nitride, and a layer of a metal. The layer of the refractory metal is deposited on the conductive surface and inner walls of the channel. The layer of the metal nitride is formed on the layer of the refractory metal. The layer of the metal nitride has a thickness extending from the layer of the refractory metal of less than 130 Å. The layer of the metal is deposited on the layer of the metal nitride.